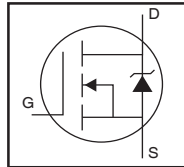


Features

- Advanced Planar Technology
- Low On-Resistance
- Logic Level Gate Drive
- Dynamic dV/dT Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified*

HEXFET® Power MOSFET



$V_{(BR)DSS}$	100V
$R_{DS(on)}$ max.	105mΩ
I_D	17A



G	D	S
Gate	Drain	Source

Description

Specifically designed for Automotive applications, this Stripe Planar design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRLR3410	D-pak	Tube	75	AUIRLR3410
		Tape and Reel	2000	AUIRLR3410TR
		Tape and Reel Left	3000	AUIRLR3410TRL
		Tape and Reel Right	3000	AUIRLR3410TRR

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	17	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	12	
I_{DM}	Pulsed Drain Current ①	60	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	79	W
	Linear Derating Factor	0.53	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
E_{AS}	Single Pulse Avalanche Energy (Thermally Limited) ②⑤	150	mJ
I_{AR}	Avalanche Current ①⑤	9.0	A
E_{AR}	Repetitive Avalanche Energy ①⑤	7.9	mJ
dv/dt	Peak Diode Recovery ③	5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ③	—	1.9	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount) ⑦	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

HEXFET® is a registered trademark of International Rectifier.

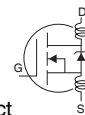
*Qualification standards can be found at <http://www.irf.com/>

Static Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

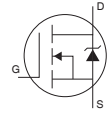
	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	100	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS/ΔT_J}	Breakdown Voltage Temp. Coefficient	—	0.122	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.105	Ω	V _{GS} = 10V, I _D = 10A ④
		—	—	0.125		V _{GS} = 5.0V, I _D = 10A ④
		—	—	0.155		V _{GS} = 4.0V, I _D = 9.0A ④
V _{GS(th)}	Gate Threshold Voltage	1.0	—	2.0	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	7.7	—	—	S	V _{DS} = 25V, I _D = 9.0A ⑤
I _{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	V _{DS} = 100V, V _{GS} = 0V
		—	—	250		V _{DS} = 80V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 16V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -16V

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

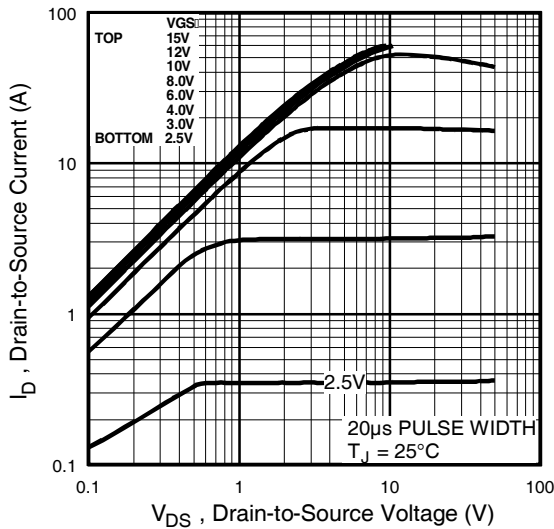
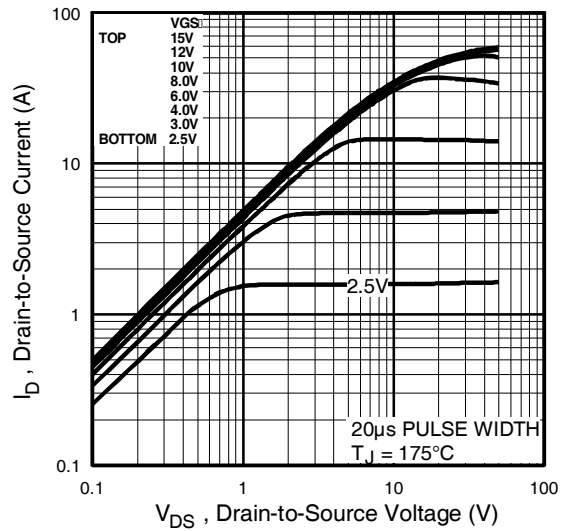
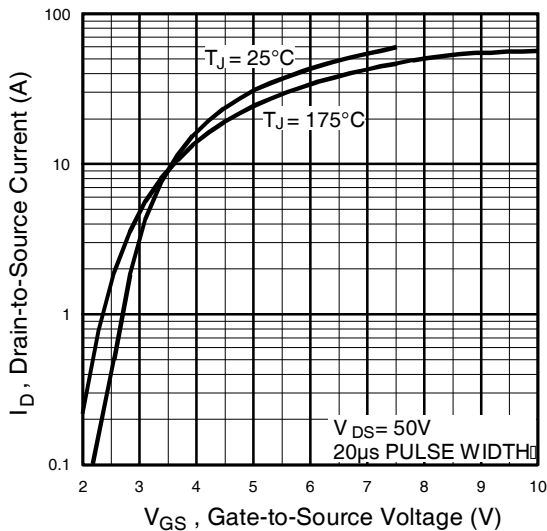
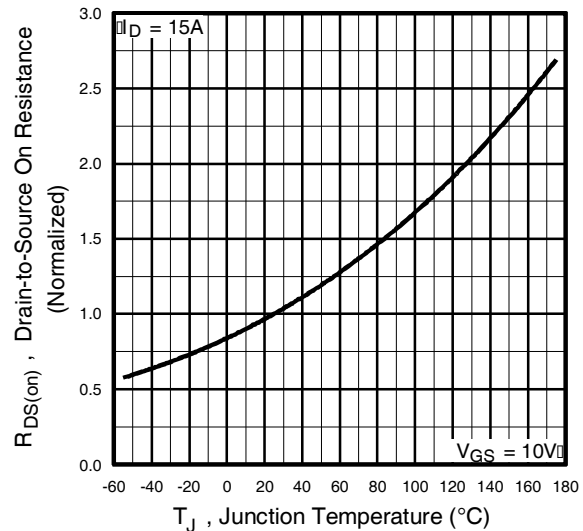
	Parameter	Min.	Typ.	Max.	Units	Conditions
Q _g	Total Gate Charge	—	—	34	nC	I _D = 9.0A V _{DS} = 80V V _{GS} = 5.0V ④⑤
Q _{gs}	Gate-to-Source Charge	—	—	4.8		
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	20		
t _{d(on)}	Turn-On Delay Time	—	7.2	—	ns	V _{DD} = 50V I _D = 9.0A R _G = 6.0 Ω V _{GS} = 5.0V ④⑤
t _r	Rise Time	—	53	—		
t _{d(off)}	Turn-Off Delay Time	—	30	—		
t _f	Fall Time	—	26	—		
L _D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L _S	Internal Source Inductance	—	7.5	—		
C _{iss}	Input Capacitance	—	800	—	pF	V _{GS} = 0V V _{DS} = 25V f = 1.0MHz ⑤
C _{oss}	Output Capacitance	—	160	—		
C _{rss}	Reverse Transfer Capacitance	—	90	—		


Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	17	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	60		
V _{SD}	Diode Forward Voltage	—	—	1.3	V	T _J = 25°C, I _S = 9.0A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	140	210	ns	T _J = 25°C, I _F = 9.0A
Q _{rr}	Reverse Recovery Charge	—	740	1100	nC	di/dt = 100A/μs ④⑤
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				


Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig.11)
- ② V_{DD} = 25V, starting T_J = 25°C, L = 3.1mH
R_G = 25Ω, I_{AS} = 9.0A. (See Figure 12)
- ③ I_{SD} ≤ 9.0A, di/dt ≤ 540A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 175°C
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ Uses IRL530N data and test conditions.
- ⑥ This is applied for L_S of D-PAK is measured between lead and center of die contact
- ⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑧ R_θ is measured at T_j approximately 90°C.


Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics

Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance Vs. Temperature

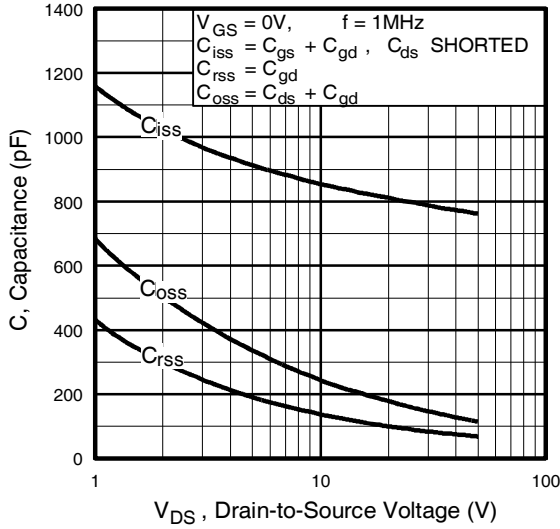


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

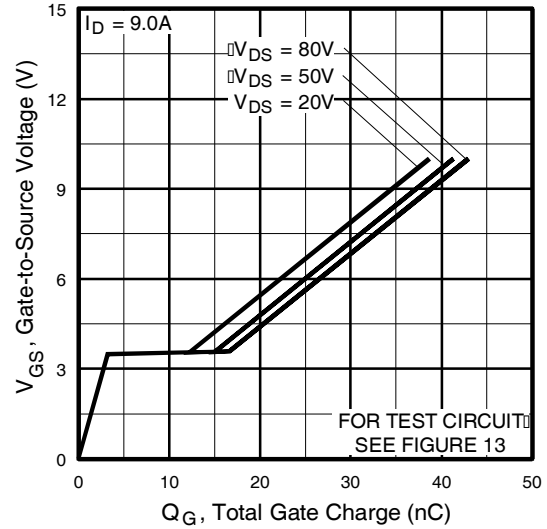


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

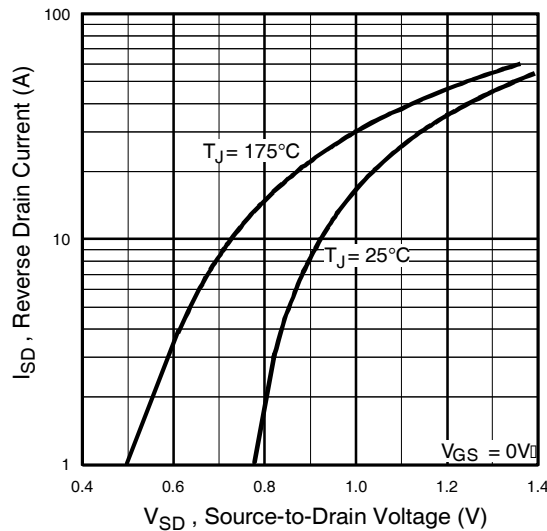


Fig 7. Typical Source-Drain Diode Forward Voltage

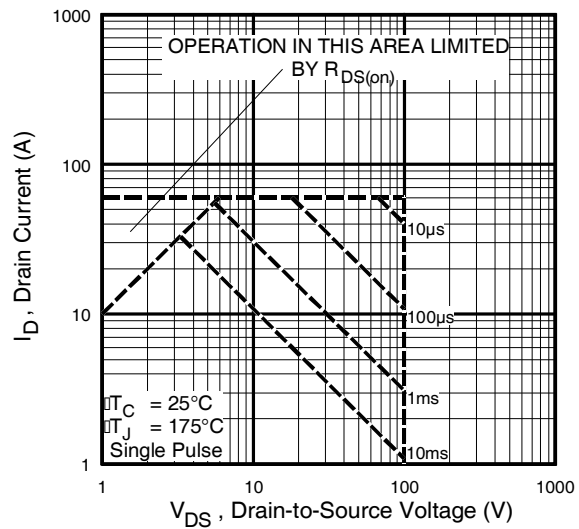


Fig 8. Maximum Safe Operating Area

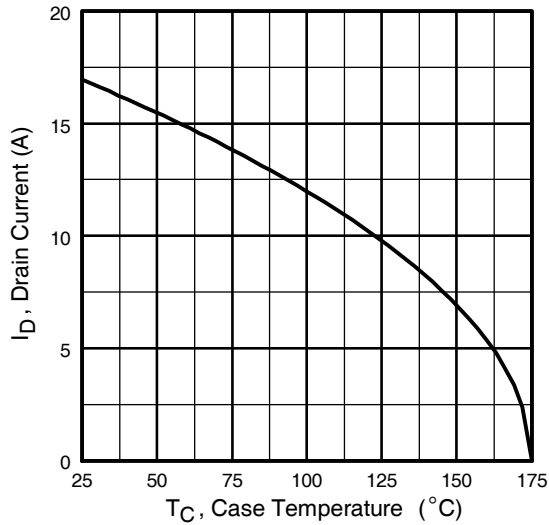


Fig 9. Maximum Drain Current Vs. Case Temperature

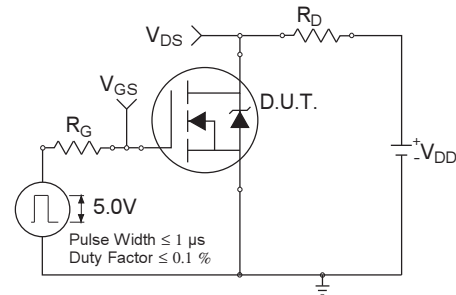


Fig 10a. Switching Time Test Circuit

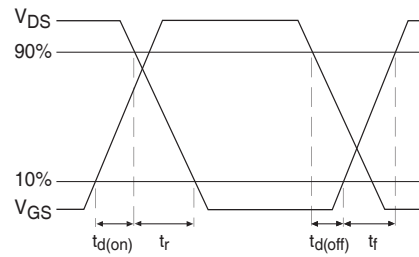


Fig 10b. Switching Time Waveforms

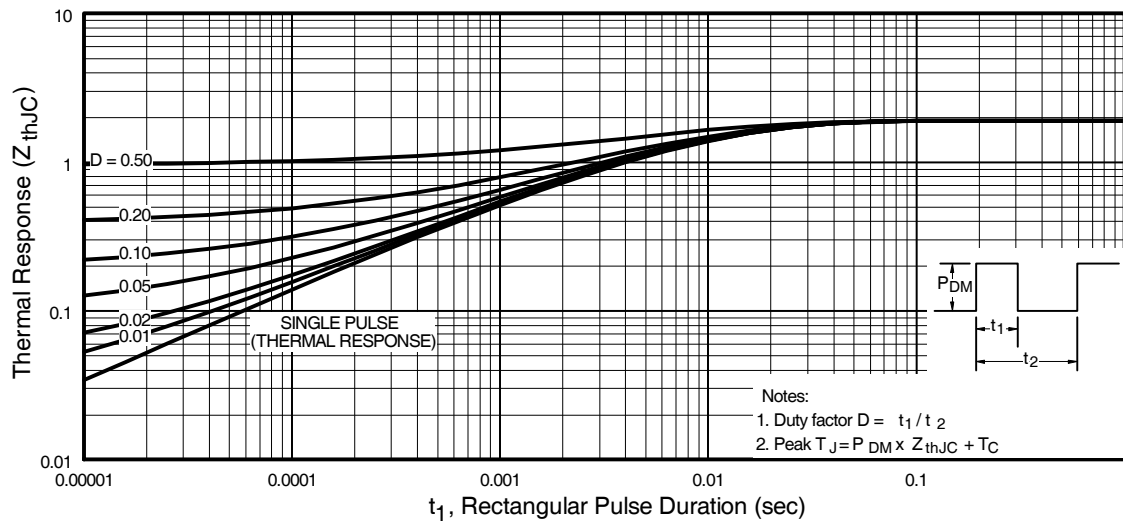
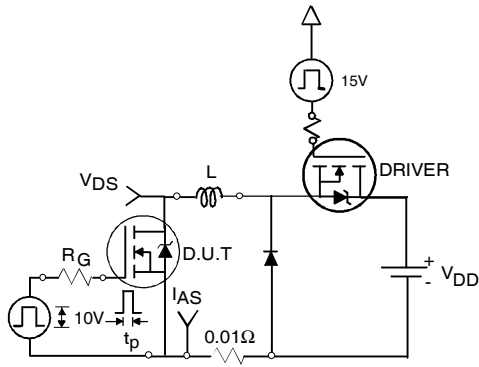
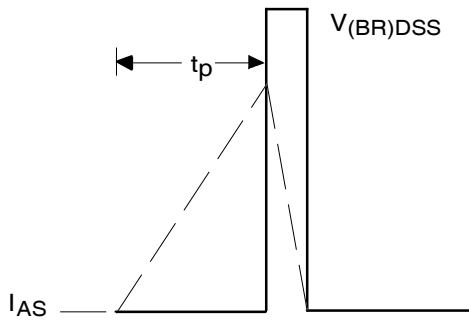
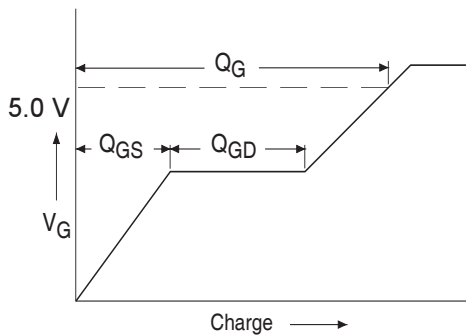
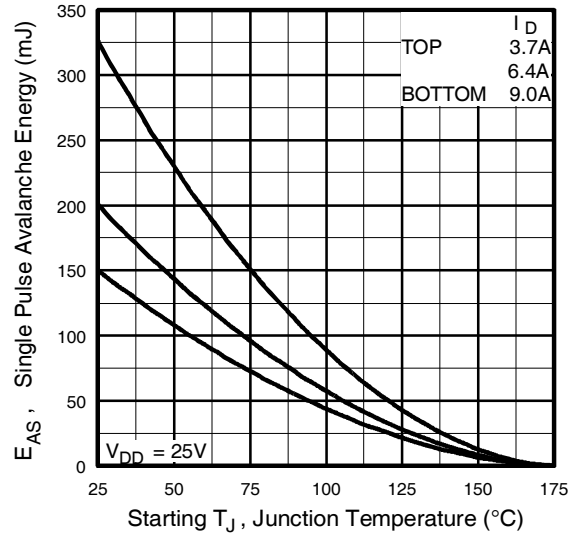
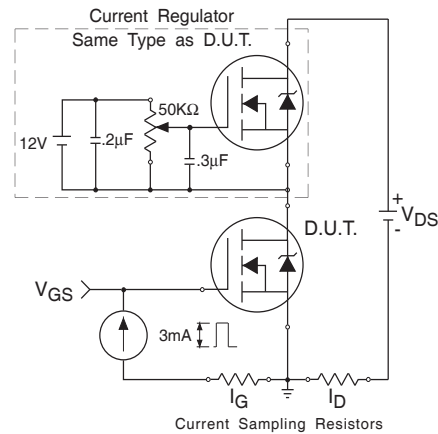
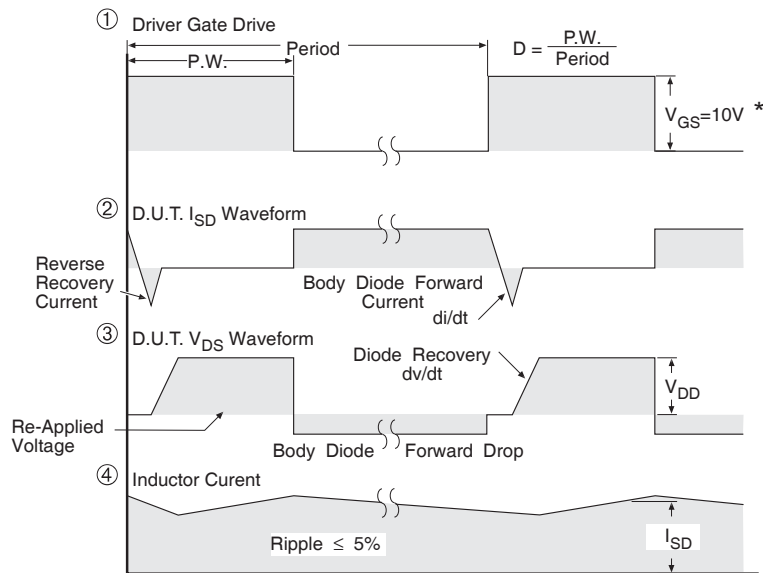
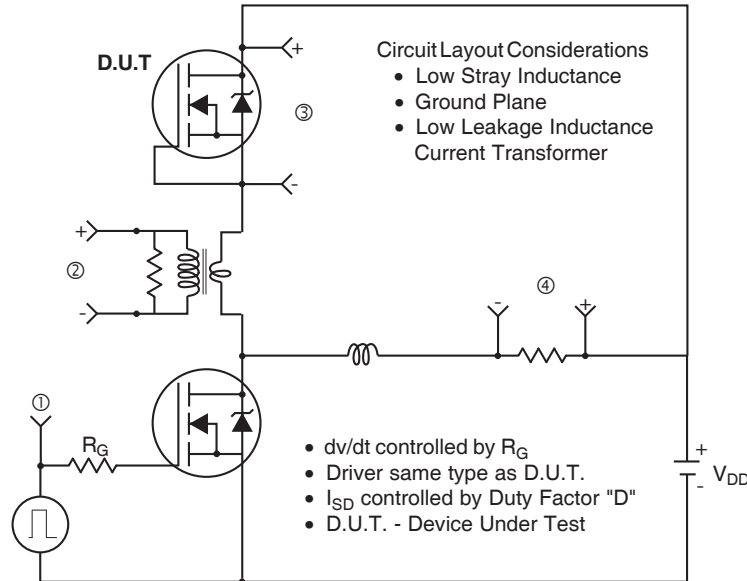


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case


Fig 12a. Unclamped Inductive Test Circuit

Fig 12b. Unclamped Inductive Waveforms

Fig 13a. Basic Gate Charge Waveform

Fig 12c. Maximum Avalanche Energy Vs. Drain Current

Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit

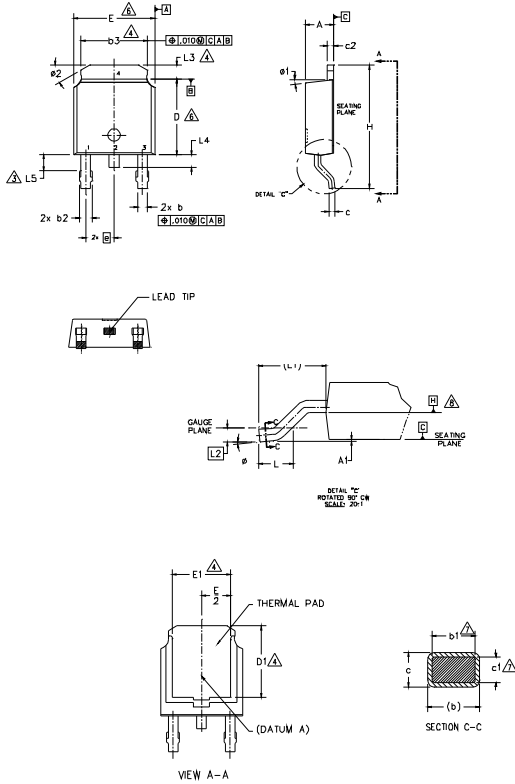


* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. For N-Channel HEXFETS

D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
- 3.- LEAD DIMENSION UNCONTROLLED IN L5.
- 4.- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
- 5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
- 6.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- 7.- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
- 8.- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
- 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	-	0.13	-	.005	
b	0.64	0.89	.025	.035	7
b1	0.65	0.79	.025	.031	7
b2	0.76	1.14	.030	.045	4
b3	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	7
c1	0.41	0.56	.016	.022	7
c2	0.46	0.89	.018	.035	6
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29 BSC	-	.090 BSC	-	
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 BSC	-	.108 REF.	-	
L2	0.51 BSC	-	.020 BSC	-	
L3	0.89	1.27	.035	.050	4
L4	-	1.02	-	.040	
L5	1.14	1.52	.045	.060	3
phi	0"	10"	0"	10"	
phi1	0"	15"	0"	15"	
phi2	25"	35"	25"	35"	

LEAD ASSIGNMENTS

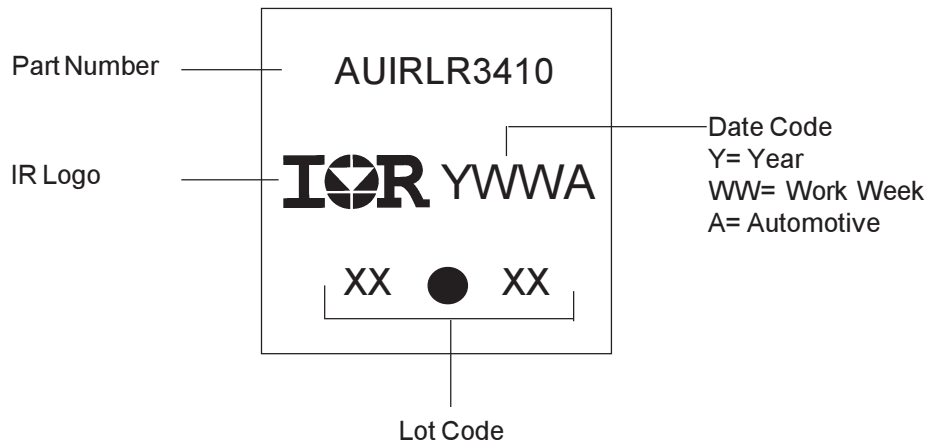
HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBT & CoPAK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

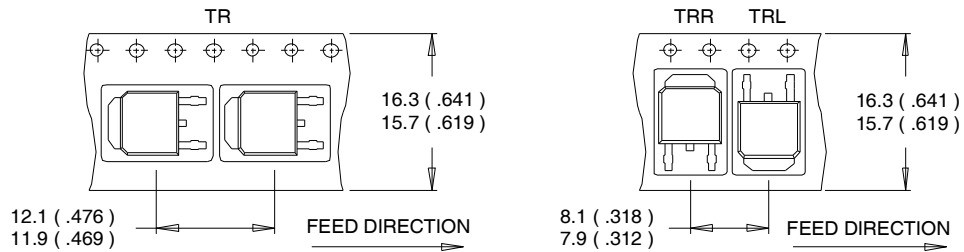
D-Pak Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

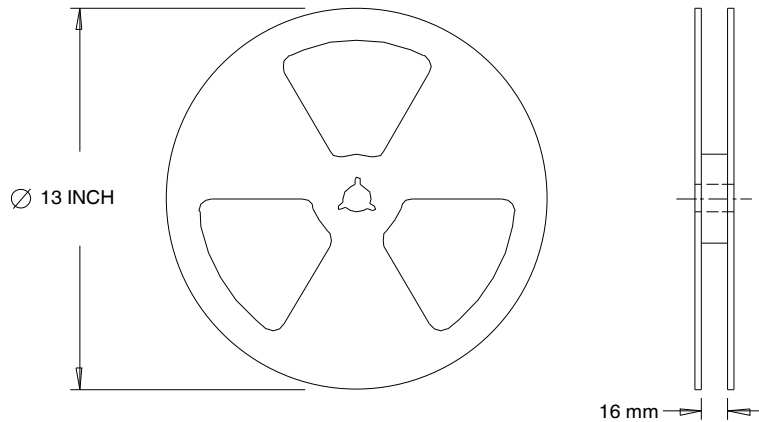
D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Qualification Information[†]

Qualification Level		Automotive (per AEC-Q101) ^{††}	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		D-PAK	MSL1
ESD	Machine Model	Class M4 AEC-Q101-002	
	Human Body Model	Class H1C AEC-Q101-001	
	Charged Device Model	Class C5 AEC-Q101-005	
RoHS Compliant		Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

†† Exceptions to AEC-Q101 requirements are noted in the qualification report.

IMPORTANT NOTICE

Unless specifically designated for the automotive market, International Rectifier Corporation and its subsidiaries (IR) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or services without notice. Part numbers designated with the “AU” prefix follow automotive industry and / or customer specific requirements with regards to product discontinuance and process change notification. All products are sold subject to IR’s terms and conditions of sale supplied at the time of order acknowledgment.

IR warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with IR’s standard warranty. Testing and other quality control techniques are used to the extent IR deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

IR assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using IR components. To minimize the risks with customer products and applications, customers should provide adequate design and operating safeguards.

Reproduction of IR information in IR data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alterations is an unfair and deceptive business practice. IR is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of IR products or serviced with statements different from or beyond the parameters stated by IR for that product or service voids all express and any implied warranties for the associated IR product or service and is an unfair and deceptive business practice. IR is not responsible or liable for any such statements.

IR products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or in other applications intended to support or sustain life, or in any other application in which the failure of the IR product could create a situation where personal injury or death may occur. Should Buyer purchase or use IR products for any such unintended or unauthorized application, Buyer shall indemnify and hold International Rectifier and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that IR was negligent regarding the design or manufacture of the product.

IR products are neither designed nor intended for use in military/aerospace applications or environments unless the IR products are specifically designated by IR as military-grade or “enhanced plastic.” Only products designated by IR as military-grade meet military specifications. Buyers acknowledge and agree that any such use of IR products which IR has not designated as military-grade is solely at the Buyer’s risk, and that they are solely responsible for compliance with all legal and regulatory requirements in connection with such use.

IR products are neither designed nor intended for use in automotive applications or environments unless the specific IR products are designated by IR as compliant with ISO/TS 16949 requirements and bear a part number including the designation “AU”. Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, IR will not be responsible for any failure to meet such requirements.

For technical support, please contact IR’s Technical Assistance Center

<http://www.irf.com/technical-info/>

WORLD HEADQUARTERS:

233 Kansas St., El Segundo, California 90245

Tel: (310) 252-7105

Revision History

Date	Comments
3/17/2014	<ul style="list-style-type: none">• Added "Logic Level Gate Drive" bullet in the features section on page 1• Updated data sheet with new IR corporate template